



# PHPT61010PY

100 V, 10 A PNP high power bipolar transistor

20 March 2015

Product data sheet

## 1. General description

PNP high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

NPN complement: PHPT61010NY.

## 2. Features and benefits

- High thermal power dissipation capability
- Suitable for high temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

## 3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications
- Motor drive
- Relay replacement

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-100	V
$I_C$	collector current		-	-	-10	A
$I_{CM}$	peak collector current	$t_p \leq 1$ ms; single pulse	-	-	-20	A
$R_{CEsat}$	collector-emitter saturation resistance	$I_C = -10$ A; $I_B = -1$ A; $t_p \leq 300$ $\mu$ s; $\delta \leq 0.02$ ; $T_{amb} = 25$ °C; pulsed	-	53	80	m $\Omega$

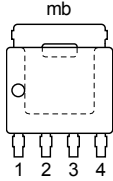
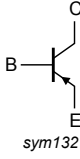


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## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter	 <p>LFPAK56; Power-SO8 (SOT669)</p>	
2	E	emitter		
3	E	emitter		
4	B	base		
mb	C	collector		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHPT61010PY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT61010PY	1010PAB

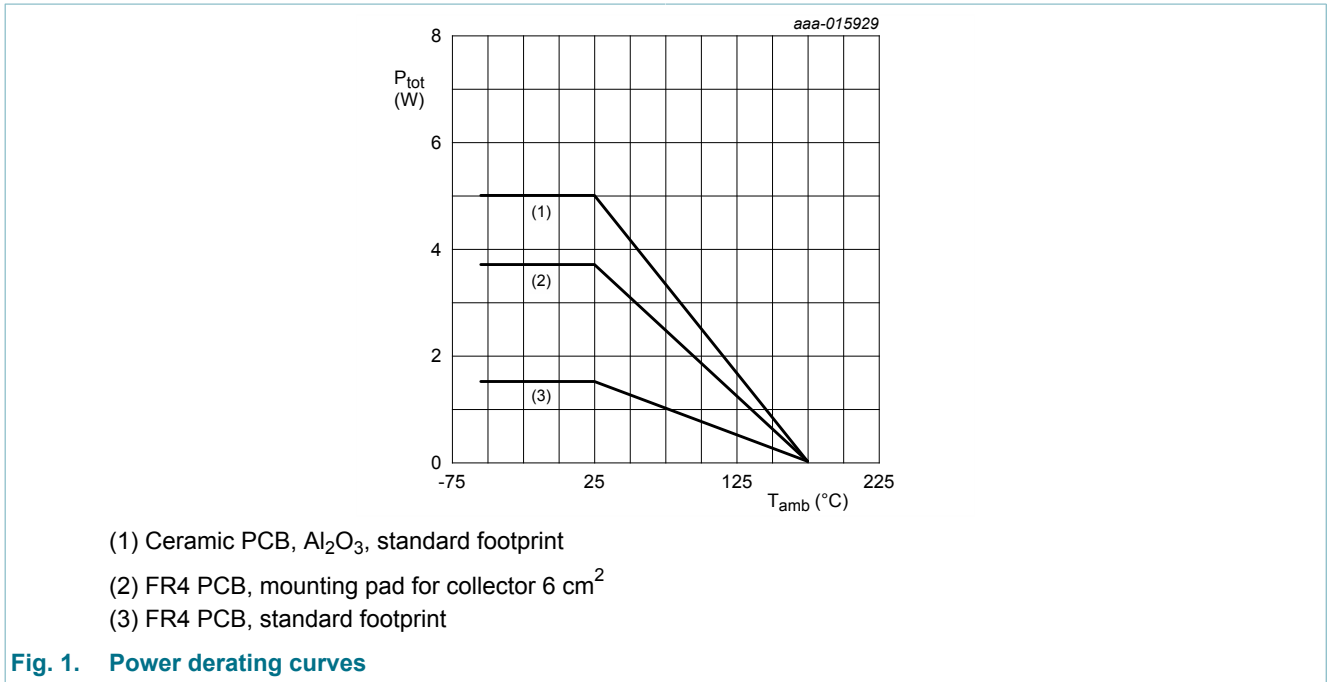
## 8. Limiting values

**Table 5. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	-100	V
$V_{CEO}$	collector-emitter voltage	open base		-	-100	V
$V_{EBO}$	emitter-base voltage	open collector		-	-8	V
$I_C$	collector current			-	-10	A
$I_{CM}$	peak collector current	$t_p \leq 1$ ms; single pulse		-	-20	A
$I_B$	base current			-	-1	A
$I_{BM}$	peak base current	$t_p \leq 1$ ms; pulsed		-	-2	A
$P_{tot}$	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	1.5	W
			[2]	-	3.7	W
			[3]	-	5	W
			[4]	-	25	W
$T_j$	junction temperature			-	175	°C
$T_{amb}$	ambient temperature			-55	175	°C
$T_{stg}$	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [4] Power dissipation from junction to mounting base.

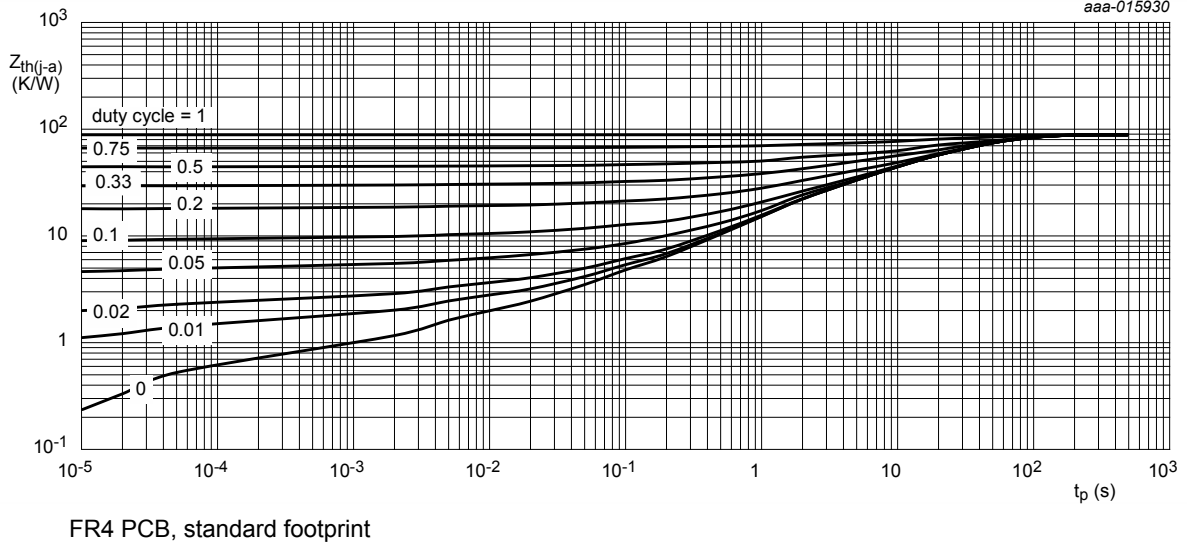


## 9. Thermal characteristics

Table 6. Thermal characteristics

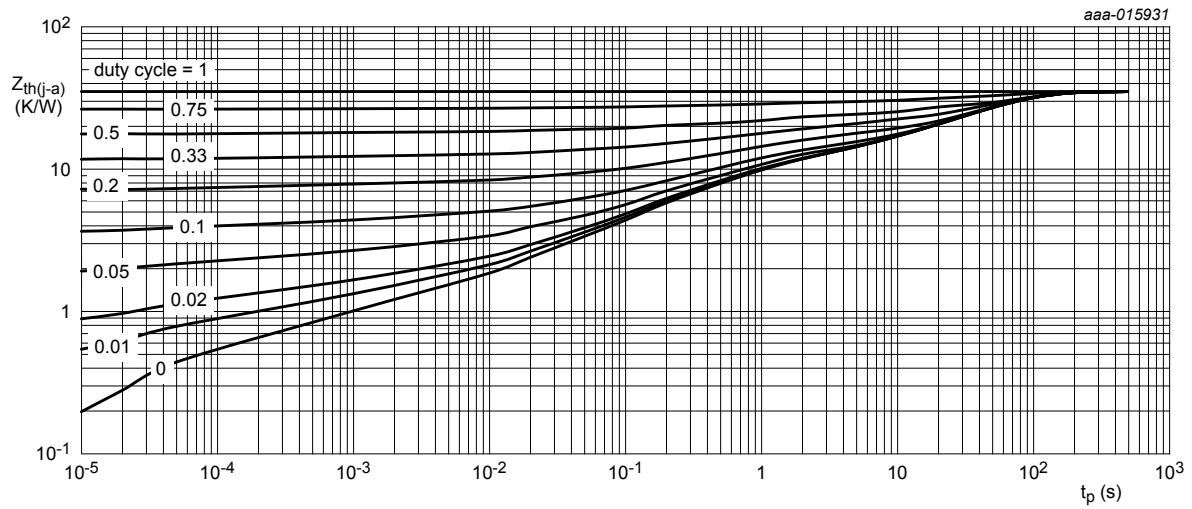
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	100	K/W
			[2]	-	-	41	K/W
			[3]	-	-	30	K/W
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base			-	-	6	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.



FR4 PCB, standard footprint

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for collector  $6 \text{ cm}^2$

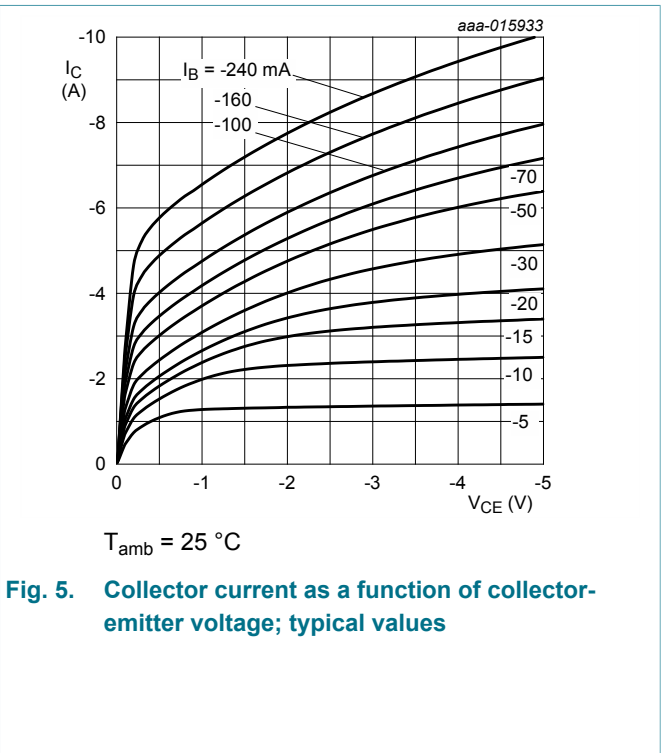
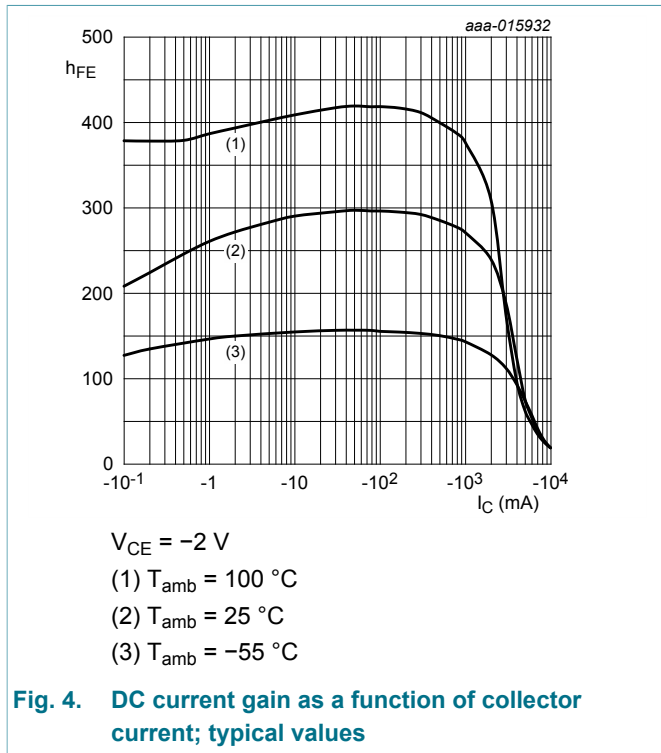
Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = -80 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
		V <sub>CB</sub> = -80 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = -80 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -8 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -2 V; I <sub>C</sub> = -0.5 A; T <sub>amb</sub> = 25 °C	180	330	-	
		V <sub>CE</sub> = -2 V; I <sub>C</sub> = -1 A; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C; pulsed	170	265	-	
		V <sub>CE</sub> = -2 V; I <sub>C</sub> = -5 A; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C; pulsed	60	75	-	
		V <sub>CE</sub> = -2 V; I <sub>C</sub> = -10 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	10	15	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = -1 A; I <sub>B</sub> = -50 mA; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-55	-90	mV
		I <sub>C</sub> = -5 A; I <sub>B</sub> = -0.5 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-160	-250	mV
		I <sub>C</sub> = -10 A; I <sub>B</sub> = -1 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-530	-800	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	I <sub>C</sub> = -10 A; I <sub>B</sub> = -1 A; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C; pulsed	-	53	80	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = -1 A; I <sub>B</sub> = -50 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-	-0.9	V
		I <sub>C</sub> = -5 A; I <sub>B</sub> = -0.5 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-	-1.1	V
		I <sub>C</sub> = -10 A; I <sub>B</sub> = -1 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-	-1.3	V
V <sub>BEon</sub>	base-emitter turn-on voltage	V <sub>CE</sub> = -2 V; I <sub>C</sub> = -0.5 A; T <sub>amb</sub> = 25 °C	-	-	-0.8	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = -12.5 V; I <sub>C</sub> = -5 A; I <sub>Bon</sub> = -250 mA; I <sub>Boff</sub> = 250 mA; T <sub>amb</sub> = 25 °C	-	20	-	ns
t <sub>r</sub>	rise time		-	145	-	ns
t <sub>on</sub>	turn-on time		-	165	-	ns
t <sub>s</sub>	storage time		-	155	-	ns
t <sub>f</sub>	fall time		-	80	-	ns
t <sub>off</sub>	turn-off time		-	235	-	ns

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$f_T$	transition frequency	$V_{CE} = -10\text{ V}; I_C = -500\text{ mA};$ $f = 100\text{ MHz}; T_{amb} = 25\text{ }^\circ\text{C}$	-	90	-	MHz
$C_c$	collector capacitance	$V_{CB} = -10\text{ V}; I_E = 0\text{ A}; i_e = 0\text{ A};$ $f = 1\text{ MHz}; T_{amb} = 25\text{ }^\circ\text{C}$	-	101	-	pF



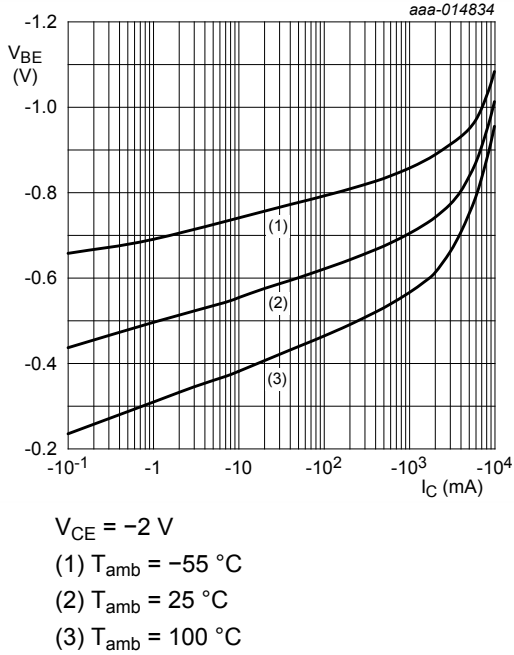


Fig. 6. Base-emitter voltage as a function of collector current; typical values

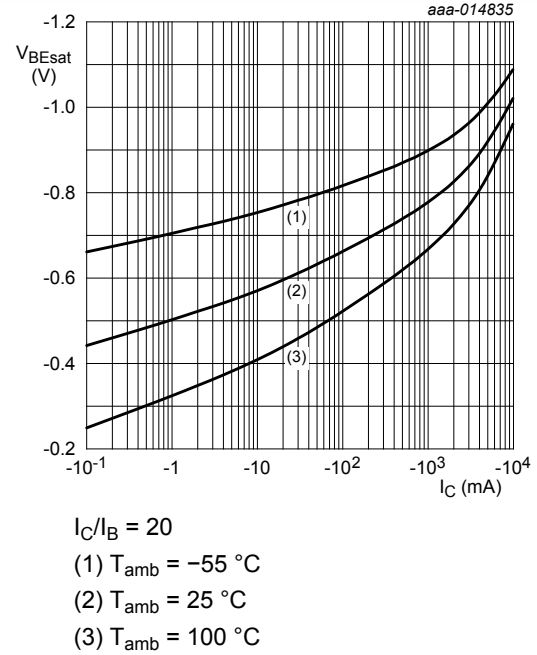


Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

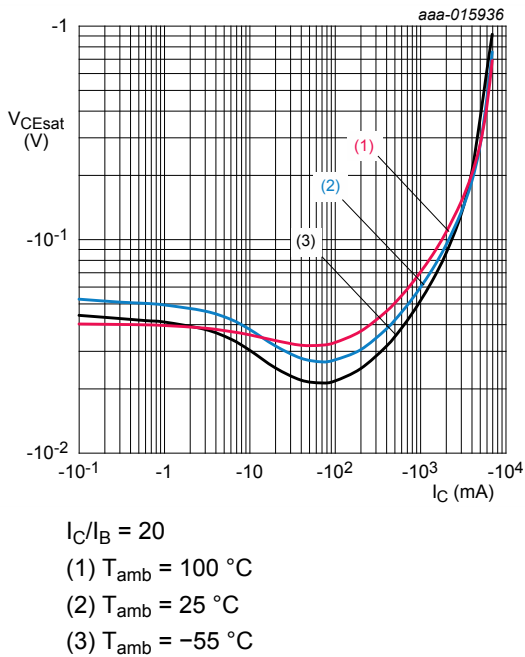


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

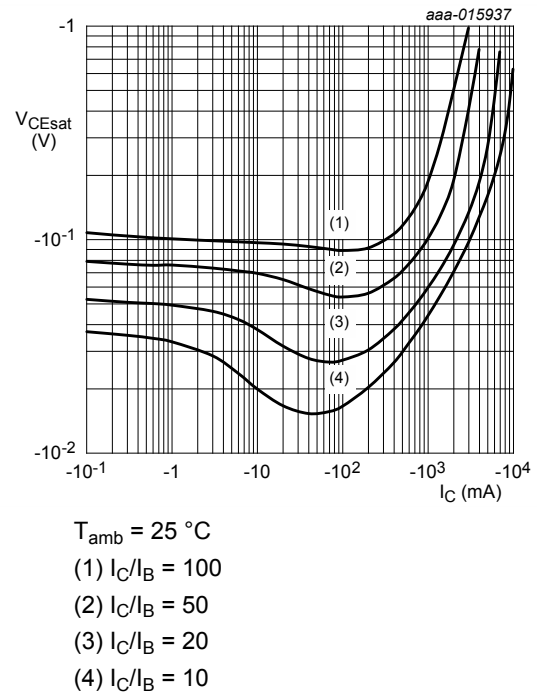
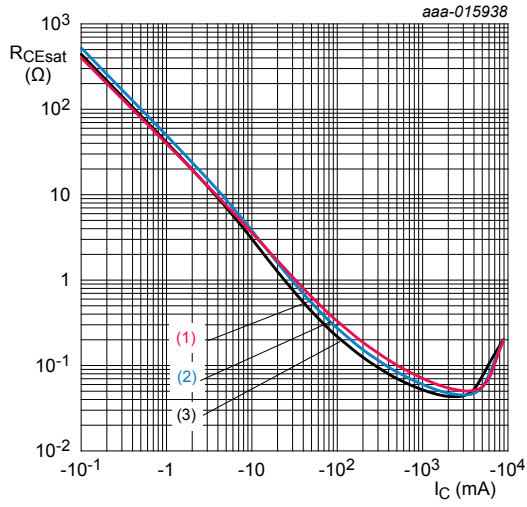


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

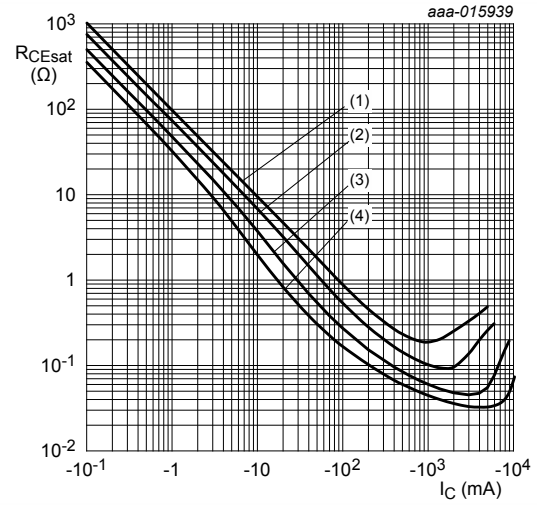




$I_C/I_B = 20$

- (1)  $T_{amb} = 100\text{ °C}$
- (2)  $T_{amb} = 25\text{ °C}$
- (3)  $T_{amb} = -55\text{ °C}$

**Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values**



$T_{amb} = 25\text{ °C}$

- (1)  $I_C/I_B = 100$
- (2)  $I_C/I_B = 50$
- (3)  $I_C/I_B = 20$
- (4)  $I_C/I_B = 10$

**Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values**

### 11. Test information

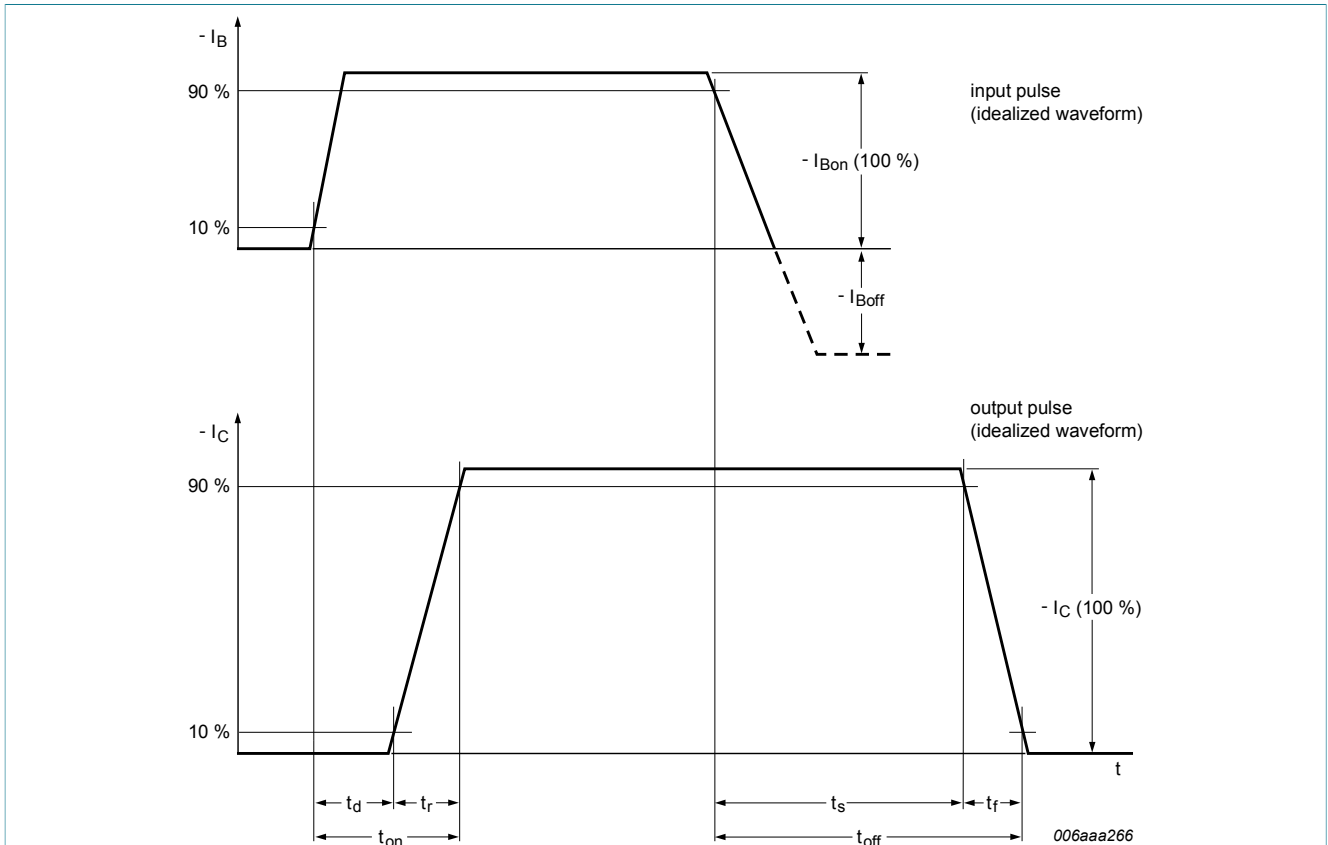


Fig. 12. BISS transistor switching time definition

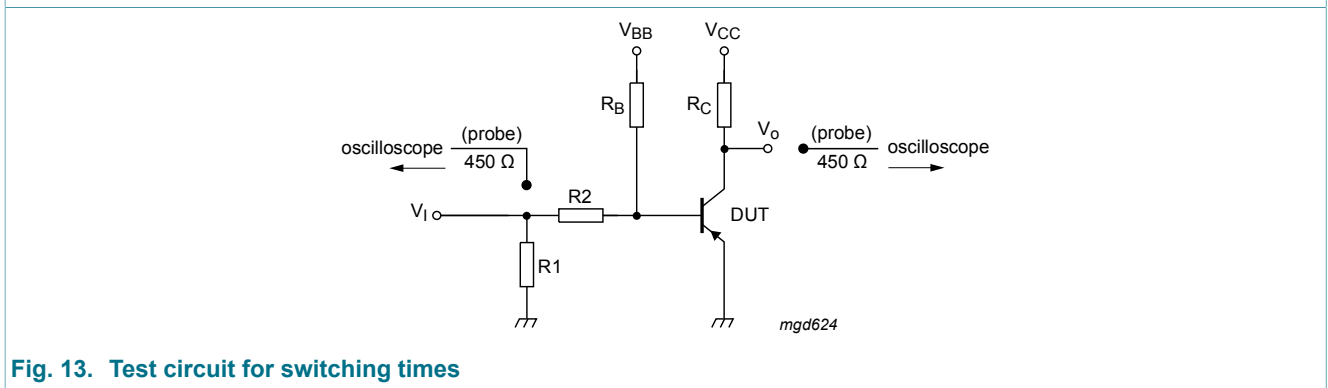


Fig. 13. Test circuit for switching times

#### 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 12. Package outline

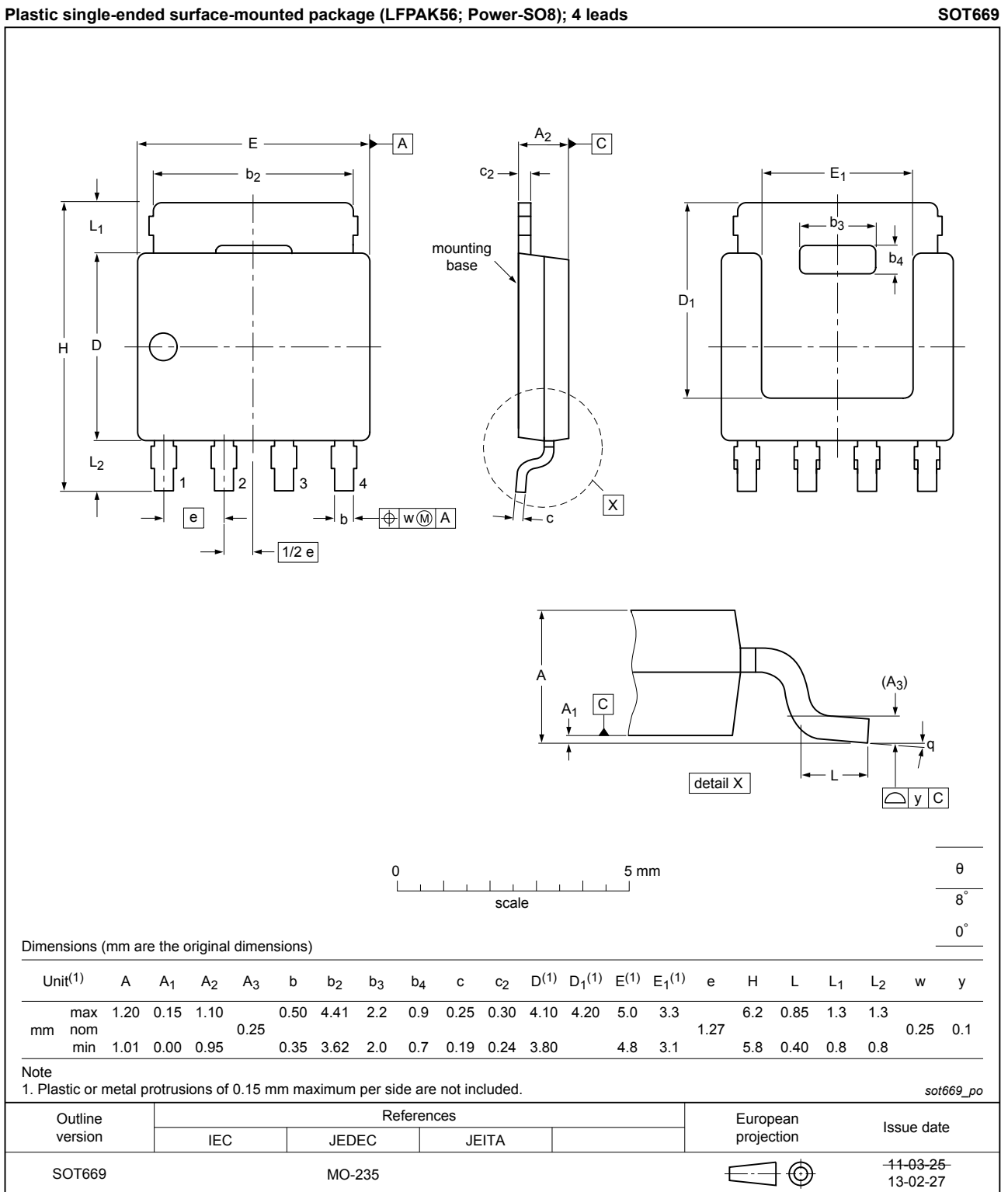


Fig. 14. Package outline LFAK56; Power-SO8 (SOT669)

### 13. Soldering

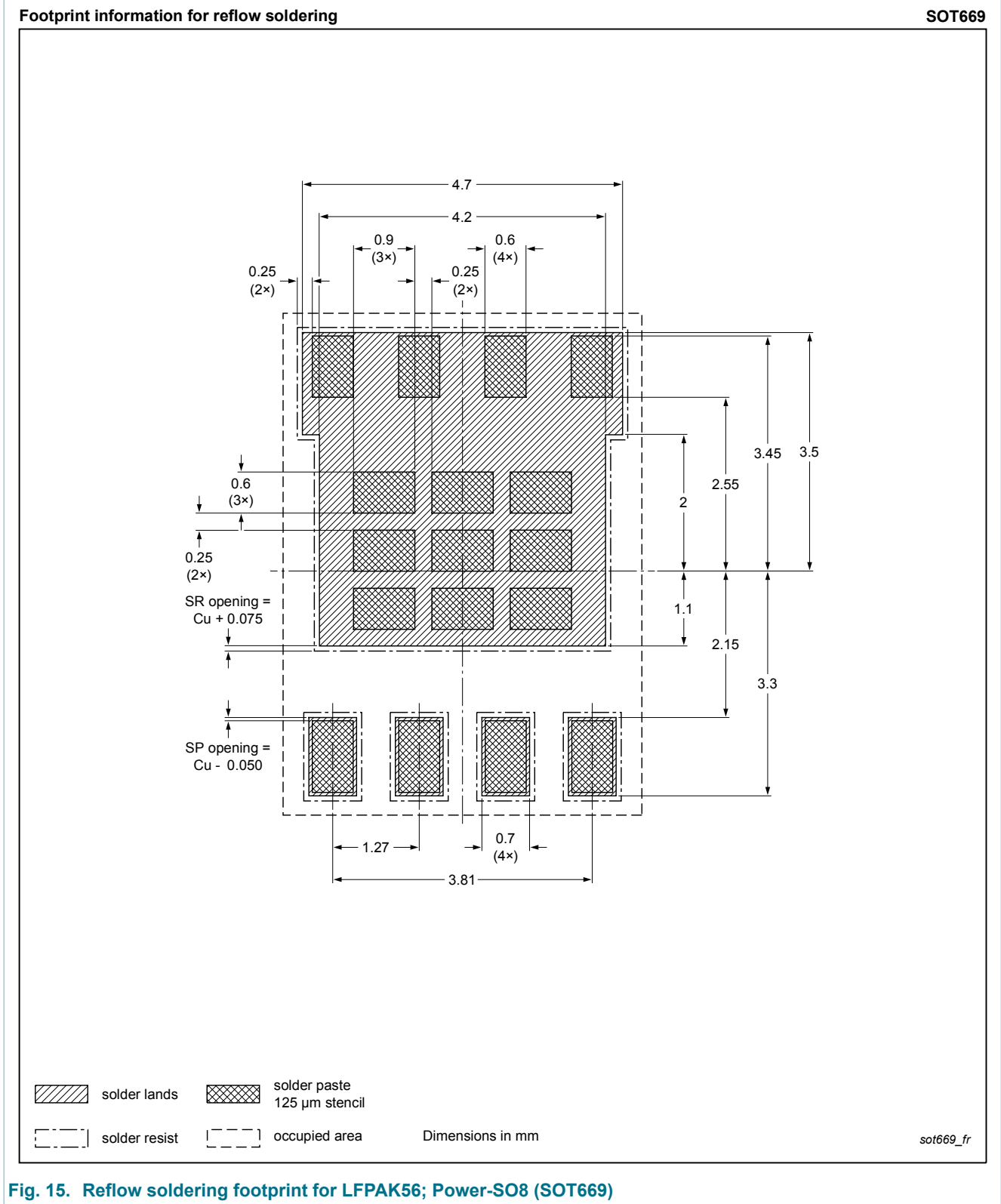


Fig. 15. Reflow soldering footprint for LFPAK56; Power-SO8 (SOT669)

## 14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT61010PY v.1	20150320	Product data sheet	-	-

## 15. Legal information

### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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## 16. Contents

1	General description .....	1
2	Features and benefits .....	1
3	Applications .....	1
4	Quick reference data .....	1
5	Pinning information .....	2
6	Ordering information .....	2
7	Marking .....	2
8	Limiting values .....	3
9	Thermal characteristics .....	4
10	Characteristics .....	6
11	Test information .....	10
11.1	Quality information .....	10
12	Package outline .....	11
13	Soldering .....	12
14	Revision history .....	13
15	Legal information .....	14
15.1	Data sheet status .....	14
15.2	Definitions .....	14
15.3	Disclaimers .....	14
15.4	Trademarks .....	15

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